

TOSHIBA**TC74LCX16373AFT**

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74LCX16373AFT

LOW-VOLTAGE 16-BIT D-TYPE LATCH

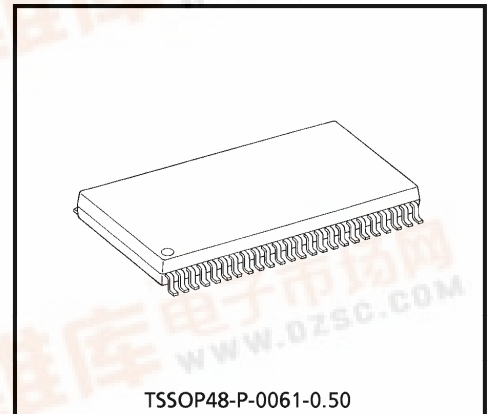
WITH 5V TOLERANT INPUTS AND OUTPUTS

The TC74LCX16373AFT is a high performance CMOS 16bit D-TYPE LATCH. Designed for use in 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

The device is designed for low-voltage (3.3V) V_{CC} applications, but it could be used to interface to 5V supply environment for both inputs and outputs.

This 16-bit D-type latch is controlled by a latch enable input (LE) and a output enable input ($\overline{OE}$) which are common to each byte. It can be used as two 8-bit latches or one 16-bit latch. When the $\overline{OE}$ input is high, the outputs are in a high impedance state.

All inputs are equipped with protection circuits against static discharge.



Weight : 0.25 g (Typ.)

PIN CONNECTION

$\overline{OE}$	1	48	1LE
1Q1	2	47	1D1
1Q2	3	46	1D2
GND	4	45	GND
1Q3	5	44	1D3
1Q4	6	43	1D4
V_{CC}	7	42	V_{CC}
1Q5	8	41	1D5
1Q6	9	40	1D6
GND	10	39	GND
1Q7	11	38	1D7
1Q8	12	37	1D8
2Q1	13	36	2D1
2Q2	14	35	2D2
GND	15	34	GND
2Q3	16	33	2D3
2Q4	17	32	2D4
V_{CC}	18	31	V_{CC}
2Q5	19	30	2D5
2Q6	20	29	2D6
GND	21	28	GND
2Q7	22	27	2D7
2Q8	23	26	2D8
$\overline{OE}$	24	25	2LE

(TOP VIEW)

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FEATURES

- Low Voltage Operation : $V_{CC} = 2.0 \sim 3.6V$
- High Speed Operation : $t_{pd} = 7.0 \text{ ns (max.)}$ at $V_{CC} = 3.0 \sim 3.6V$
- Output Current : $|I_{OH}| / I_{OL} = 24\text{mA (min.)}$ at $V_{CC} = 3.0V$
- Latch-up Performance : $\pm 500\text{mA}$
- Package : TSSOP
(Thin Shrink Small Outline Package)
- Power Down Protection is provided on all inputs and outputs.

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TRUTH TABLE

INPUT			OUTPUT
1OE	1LE	1D1-1D8	1Q1-1Q8
H	X	X	Z
L	L	X	Qn
L	H	L	L
L	H	H	H

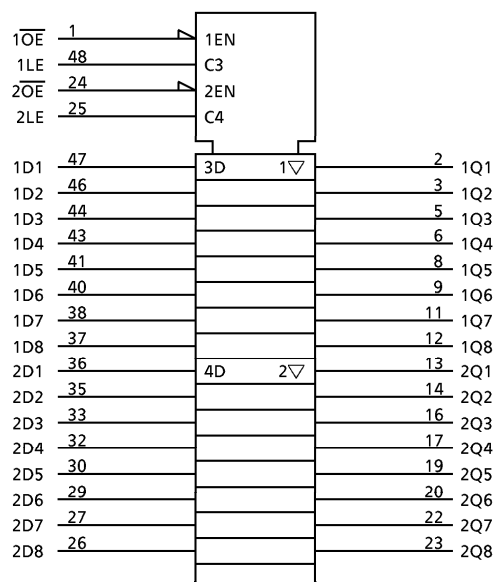
INPUT			OUTPUT
2OE	2LE	2D1-2D8	2Q1-2Q8
H	X	X	Z
L	L	X	Qn
L	H	L	L
L	H	H	H

X : Don't Care

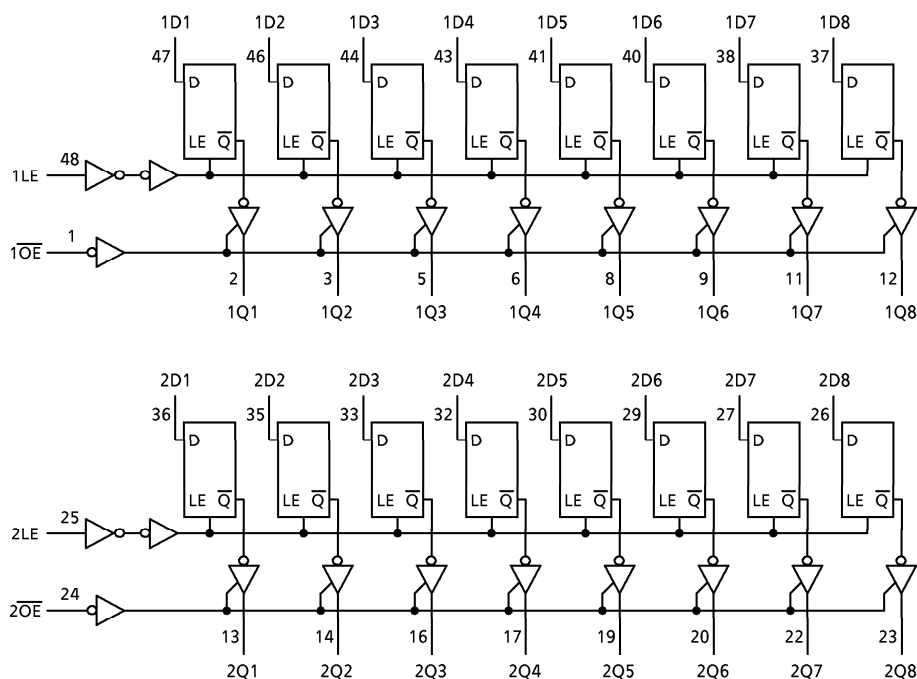
Z : High impedance

Qn : No change

IEC LOGIC SYMBOL



SYSTEM DIAGRAM



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MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT
Power Supply Voltage	V_{CC}	$-0.5 \sim 7.0$	V
Input Voltage	V_{IN}	$-0.5 \sim 7.0$	V
Output Voltage	V_{OUT}	$-0.5 \sim 7.0$ (Note 1) $-0.5 \sim V_{CC} + 0.5$ (Note 2)	V
Input Diode Current	I_{IK}	-50	mA
Output Diode Current	I_{OK}	± 50 (Note 3)	mA
DC Output Current	I_{OUT}	± 50	mA
Power Dissipation	P_D	400	mW
DC V_{CC} / Ground Current Per Supply Pin	I_{CC} / I_{GND}	± 100	mA
Storage Temperature	T_{stg}	$-65 \sim 150$	$^{\circ}\text{C}$

(Note 1) Output in Off-State

(Note 2) High or Low State. I_{OUT} absolute maximum rating must be observed.(Note 3) $V_{OUT} < \text{GND}$, $V_{OUT} > V_{CC}$

RECOMMENDED OPERATING RANGE

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	$2.0 \sim 3.6$ $1.5 \sim 3.6$ (Note 4)	V
Input Voltage	V_{IN}	$0 \sim 5.5$	V
Output Voltage	V_{OUT}	$0 \sim 5.5$ (Note 5) $0 \sim V_{CC}$ (Note 6)	V
Output Current	I_{OH} / I_{OL}	± 24 (Note 7) ± 12 (Note 8)	mA
Operating Temperature	T_{opr}	$-40 \sim 85$	$^{\circ}\text{C}$
Input Rise And Fall Time	dt / dv	$0 \sim 10$ (Note 9)	ns / V

(Note 4) Data Retention Only

(Note 5) Output in Off-State

(Note 6) High or Low State

(Note 7) $V_{CC} = 3.0 \sim 3.6\text{V}$ (Note 8) $V_{CC} = 2.7 \sim 3.0\text{V}$ (Note 9) $V_{IN} = 0.8 \sim 2.0\text{V}$, $V_{CC} = 3.0\text{V}$

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = -40~85°C)

PARAMETER		SYMBOL	TEST CONDITION		V _{CC} (V)	MIN.	MAX.	UNIT
Input Voltage	"H" Level	V _{IH}			2.7~3.6	2.0	—	V
	"L" Level	V _{IL}			2.7~3.6	—	0.8	V
Output Voltage	"H" Level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = - 100μA	2.7~3.6	V _{CC} - 0.2	—	V
				I _{OH} = - 12μA	2.7	2.2	—	
				I _{OH} = - 18mA	3.0	2.4	—	
				I _{OH} = - 24mA	3.0	2.2	—	
	"L" Level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100μA	2.7~3.6	—	0.2	V
				I _{OL} = 12mA	2.7	—	0.4	
				I _{OL} = 16mA	3.0	—	0.4	
				I _{OL} = 24mA	3.0	—	0.55	
Input Leakage Current		I _{IN}	V _{IN} = 0~5.5V	2.7~3.6	—	± 5.0	μA	
3-State Output Off-State Current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~5.5V	2.7~3.6	—	± 5.0	μA	
Power Off Leakage Current		I _{OFF}	V _{IN} / V _{OUT} = 5.5V	0	—	10.0	μA	
Quiescent Supply Current		I _{CC}	V _{IN} = V _{CC} or GND	2.7~3.6	—	20.0	μA	
			V _{IN} / V _{OUT} = 3.6~5.5V	2.7~3.6	—	± 20.0		
Increase In I _{CC} Per Input		ΔI _{CC}	V _{IH} = V _{CC} - 0.6V	2.7~3.6	—	500	μA	

AC characteristics (Ta = -40~85°C)

PARAMETER	SYMBOL	TEST CONDITION	V _{CC} (V)	MIN.	MAX.	UNIT
Propagation Delay Time (D-Q)	t _{pLH}	(Fig.1, 2)	2.7	—	8.0	ns
	t _{pHL}		3.3 ± 0.3	1.5	7.0	
Propagation Delay Time (LE-Q)	t _{pLH}	(Fig.1, 2)	2.7	—	8.0	ns
	t _{pHL}		3.3 ± 0.3	1.5	7.0	
3-State Output Enable Time	t _{pZL}	(Fig.1, 3)	2.7	—	8.2	ns
	t _{pZH}		3.3 ± 0.3	1.5	7.2	
3-State Output Disable Time	t _{pLZ}	(Fig.1, 3)	2.7	—	8.2	ns
	t _{pHZ}		3.3 ± 0.3	1.5	7.2	
Minimum Pulse Width (LE)	t _{w(H)}	(Fig.1, 2)	2.7	4.0	—	ns
			3.3 ± 0.3	3.0	—	
Minimum Set-up Time	t _s	(Fig.1, 2)	2.7	2.5	—	ns
			3.3 ± 0.3	2.5	—	
Minimum Hold Time	t _h	(Fig.1, 2)	2.7	1.5	—	ns
			3.3 ± 0.3	1.5	—	
Output To Output Skew	t _{osLH}	(Note 10)	2.7	—	—	ns
	t _{osHL}		3.3 ± 0.3	—	1.0	

(Note 10) Parameter guaranteed by design.

$$(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$$

Dynamic switching characteristics

(Ta = 25°C, Input t_r = t_f = 2.5ns, C_L = 50pF, R_L = 500Ω)

PARAMETER	SYMBOL	TEST CONDITION	V _{CC} (V)	TYP	UNIT
Quiet Output Maximum Dynamic V _{OL}	V _{OLP}	V _{IH} = 3.3V, V _{IL} = 0V	3.3	0.8	V
Quiet Output Minimum Dynamic V _{OL}	V _{OLV}	V _{IH} = 3.3V, V _{IL} = 0V	3.3	0.8	V

Capacitive characteristics (Ta = 25°C)

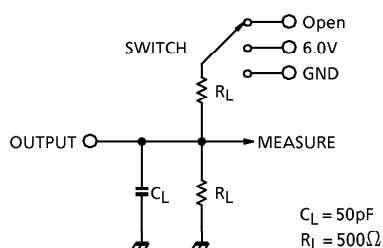
PARAMETER	SYMBOL	TEST CONDITION	V _{CC} (V)	TYP	UNIT
Input Capacitance	C _{IN}	—	3.3	7	pF
Output Capacitance	C _{OUT}		3.3	8	pF
Power Dissipation Capacitance	C _{PD}	f _{IN} = 10MHz (Note 11)	3.3	25	pF

(Note 11) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC(opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 16. \text{ (Per bit)}$$

Fig.1 Test circuit



PARAMETER	SWITCH
t_{pLH}, t_{pHL}	Open
t_{pLZ}, t_{pZL}	6.0V
t_{pHZ}, t_{pZH}	GND
t_w, t_s, t_h	Open

AC WAVEFORM

Fig.2 t_{pLH} , t_{pHL} , t_w , t_s , t_h

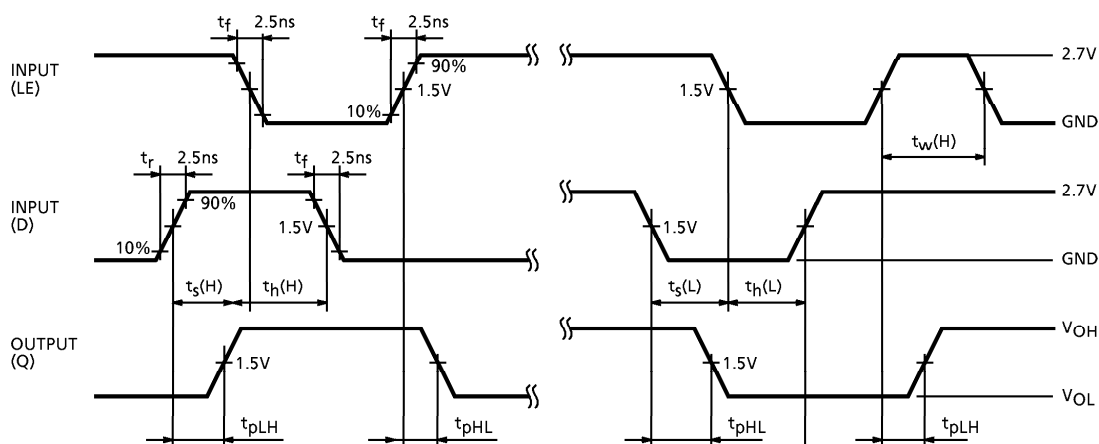
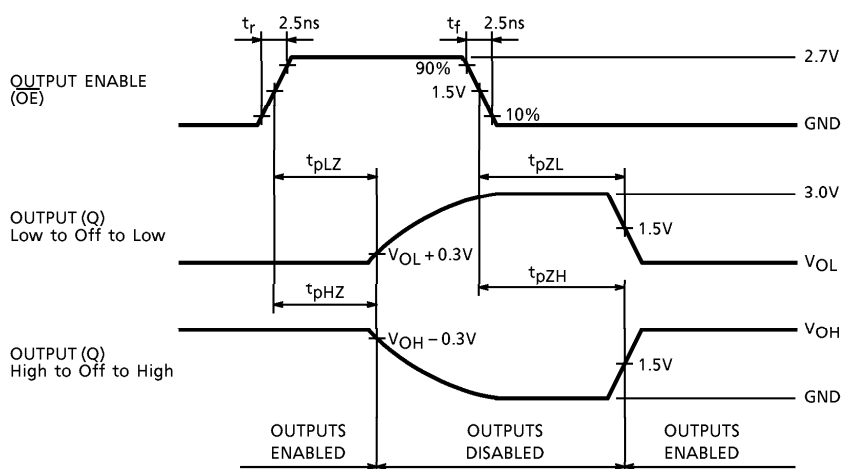


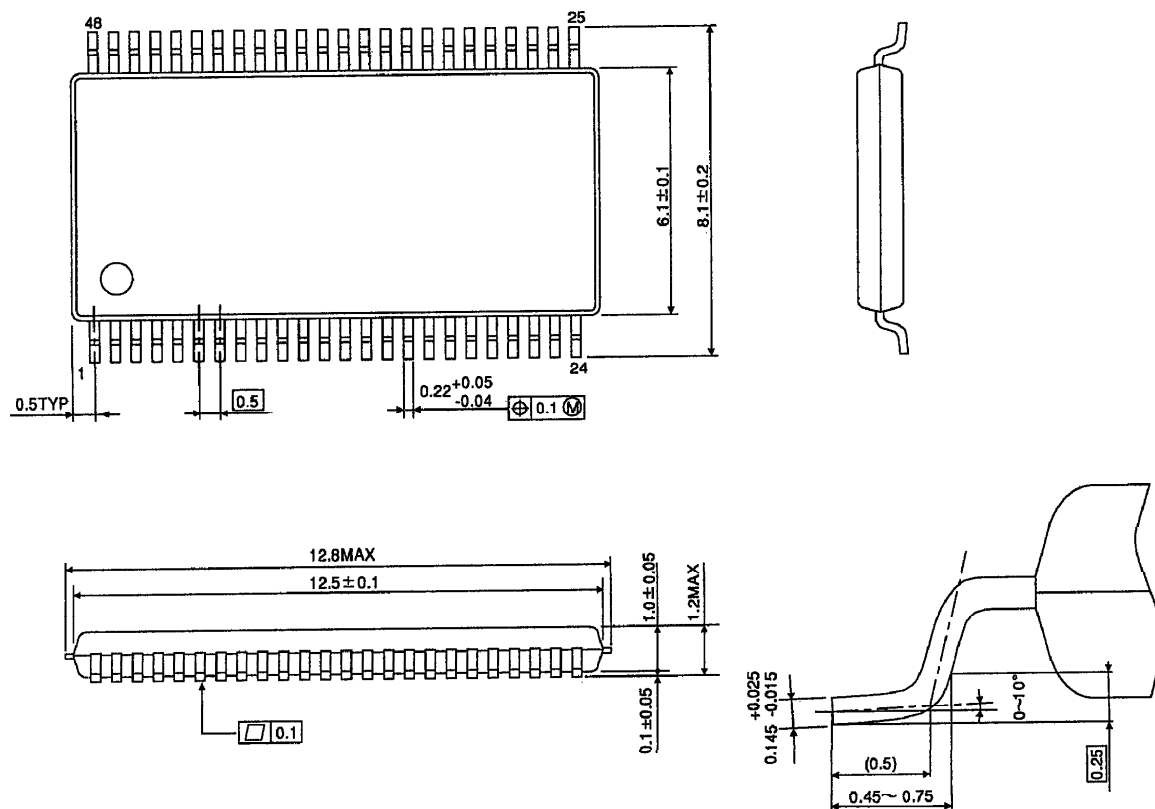
Fig.3 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}



OUTLINE DRAWING

TSSOP48-P-0061-0.50

Unit : mm



Weight : 0.25g (Typ.)